

CLAIMS

1. A method of production of a silicon carbide single crystal by precipitation from a solution using a temperature gradient furnace giving a temperature gradient to a columnar workpiece in its longitudinal direction, comprising:

5 using as said temperature gradient furnace a temperature gradient furnace provided with heat insulating walls surrounding an outer circumference of said columnar workpiece, a heating unit for heating a bottom end of said columnar workpiece through a heating susceptor, and a cooling unit for cooling a top end of said columnar workpiece through a cooling susceptor;

10 stacking, inside said furnace in order from the bottom, a source material rod comprised of silicon carbide, a solvent, a seed crystal, and a support rod supporting said seed crystal at its bottom end so as to form said columnar workpiece, heating a bottom end of said source material rod as said bottom end of the 15 columnar workpiece by said heating unit, and cooling a top end of said support rod as said top end of the columnar workpiece by said cooling unit so as to form a temperature gradient inside said columnar workpiece so that the top end face becomes lower in temperature than 20 the bottom end face of said solvent; and

25 causing a silicon carbide single crystal to grow continuously to the bottom starting from said seed crystal, wherein said method further comprises:

30 using an inside cylindrical susceptor tightly surrounding the outer circumference of said columnar workpiece.

2. A method of production of a silicon carbide single crystal as set forth in claim 1, further comprising carrying said inner cylindrical susceptor at 35 its bottom end on the top end of said source material rod and suspending said support rod by a ring-shaped member screwed over its top outer circumference from the top end

of said inner cylindrical susceptor so as to hold it in a manner adjustable in vertical position.

5 3. A method of production of a silicon carbide single crystal as set forth in claim 1 or 2, further comprising using as said source material rod a source material rod provided with one of a cylindrical or spherical counter bore at its top face.

10 4. A method of production of a silicon carbide single crystal as set forth in any one of claims 1 to 3, further comprising using as said solvent one comprised of Si and at least one type of coexisting element selected from Y, Sc, a lanthanoid, an element of Group I of the Periodic Table, and an element of Group II of the Periodic Table.

15 5. A method of production of a silicon carbide single crystal by precipitation from a solution using a temperature gradient furnace giving a temperature gradient to a columnar workpiece in its longitudinal direction, comprising:

20 using as said temperature gradient furnace a temperature gradient furnace provided with heat insulating walls surrounding an outer circumference of said columnar workpiece, a heating unit for heating a bottom end of said columnar workpiece through a heating susceptor, and a cooling unit for cooling a top end of said columnar workpiece through a cooling susceptor;

25 stacking, inside said furnace in order from the bottom, a source material rod comprised of silicon carbide, a solvent, a seed crystal, and a support rod supporting said seed crystal at its bottom end so as to form said columnar workpiece, heating a bottom end of said source material rod as said bottom end of the columnar workpiece by said heating unit, and cooling a top end of said support rod as said top end of the columnar workpiece by said cooling unit so as to form a temperature gradient inside said columnar workpiece so that the top end face becomes lower in temperature than

the bottom end face of said solvent; and
causing a silicon carbide single crystal
to grow continuously to the bottom starting from said
seed crystal, wherein said method further comprises:

5 using as said source material rod a source
material rod provided with a counter bore of an inside
diameter equal to an outside diameter of said seed
crystal on the top face and pulling said support rod at
the time where a predetermined thickness of the single
10 crystal is grown so as to remove said single crystal from
said solvent.

6. A method of production of a silicon carbide
single crystal as set forth in claim 5, further
comprising surrounding said columnar workpiece with an
15 heat insulating cylinder interposed between said heat
insulating walls and said columnar workpiece, making a
bottom end part of said support rod to have a shape with
an outside diameter larger than other parts of said
columnar workpiece, and bringing an outer circumferential
20 face of the bottom end part of said support rod into
contact with an inner circumferential face of said heat
insulating cylinder.

7. A method of production of a silicon carbide
single crystal as set forth in claim 5 or 6, further
comprising using a top end holder of said support rod
25 provided with a buffer mechanism allowing free rise of
said support rod.